

MAC229A8FP, MAC229A10FP




ON Semiconductor

<http://onsemi.com>

Triacs Silicon Bidirectional Thyristors

Designed primarily for industrial and consumer applications for full wave control of ac loads such as appliance controls, heater controls, motor controls, and other power switching applications.

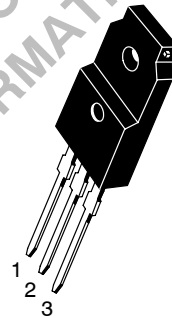
- All Diffused and Glass-Passivated Junctions for Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance and High Heat Dissipation
- Center Gate Geometry for Uniform Current Spreading
- Gate Triggering Guaranteed in Four Modes
-  Indicates UL Registered — File #E69369
- Device Marking: Logo, Device Type, e.g., MAC229A8FP, Date Code

ISOLATED TRIAC (RL)
8 AMPERES RMS
600 thru 800 VOLTS



MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage ⁽¹⁾ ($T_J = -40$ to 110°C , Sine Wave 50 to 60 Hz, Gate Open) MAC229A8FP MAC229A10FP	V_{DRM} , V_{RRM}	600 800	Volts
On-State RMS Current ($T_C = 80^\circ\text{C}$) Full Cycle Sine Wave 50 to 60 Hz	$I_{\text{T(RMS)}}$	8.0	Amps
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, $T_J = 110^\circ\text{C}$)	I_{TSM}	80	Amps
Circuit Fusing Consideration ($t = 8.3$ ms)	I^2t	26	A^2s
Peak Gate Current ($t \leq 2 \mu\text{s}$, $T_C = 80^\circ\text{C}$)	I_{GM}	± 2.0	Amps
Peak Gate Voltage ($t \leq 2 \mu\text{s}$, $T_C = 80^\circ\text{C}$)	V_{GM}	± 10	Volts
Peak Gate Power ($t \leq 2 \mu\text{s}$, $T_C = 80^\circ\text{C}$)	P_{GM}	20	Watts
Average Gate Power ($T_C = 80^\circ\text{C}$, $t \leq 8.3$ ms)	$P_{\text{G(AV)}}$	0.5	Watt
RMS Isolation Voltage ($T_A = 25^\circ\text{C}$, Relative Humidity $\leq 20\%$) (RL)	$V_{\text{(ISO)}}$	1500	Volts
Operating Junction Temperature Range	T_J	-40 to 110	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 to 150	$^\circ\text{C}$
Mounting Torque	—	8.0	in. lb.



ISOLATED TO-220 Full Pack
CASE 221C
STYLE 3

PIN ASSIGNMENT	
1	Main Terminal 1
2	Main Terminal 2
3	Gate

ORDERING INFORMATION

Device	Package	Shipping
MAC229A8FP	ISOLATED TO220FP	500/Box
MAC229A10FP	ISOLATED TO220FP	500/Box

(1) V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

(2) The case temperature reference point for all TC measurements is a point on the center lead of the package as close as possible to the plastic body.

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THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.2	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Case to Sink	$R_{\theta CS}$	2.2	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	$^{\circ}\text{C}/\text{W}$
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	T_L	260	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}\text{C}$ unless otherwise noted; Electricals apply in both directions)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Peak Repetitive Blocking Current ⁽¹⁾ ($V_D = \text{Rated } V_{DRM}, V_{RRM}; \text{ Open Gate}$)	I_{DRM}, I_{RRM}	—	—	10	μA
		—	—	2.0	mA

ON CHARACTERISTICS

Peak On-State Voltage ($I_{TM} = \pm 11 \text{ A Peak, Pulse Width} \leq 2 \text{ ms, Duty Cycle} \leq 2\%$)	V_{TM}	—	—	1.8	Volts
Gate Trigger Current (Continuous dc) ($V_D = 12 \text{ V, } R_L = 100 \Omega$) MT2(+), G(+); MT2(+), G(-); MT2(-), G(-) MT2(-), G(+)	I_{GT}	—	—	10 20	mA
Gate Trigger Voltage (Continuous dc) ($V_D = 12 \text{ V, } R_L = 100 \Omega$) MT2(+), G(+); MT2(+), G(-); MT2(-), G(-) MT2(-), G(+)	V_{GT}	—	—	2.0 2.5	Volts
Gate Non-Trigger Voltage (Continuous dc) ($V_D = 12 \text{ V, } T_C = 110^{\circ}\text{C, } R_L = 100 \Omega$) All Four Quadrants	V_{GD}	0.2	—	—	Volts
Holding Current ($V_D = 12 \text{ Vdc, Initiating Current} = \pm 200 \text{ mA, Gate Open}$)	I_H	—	—	15	mA
Gate-Controlled Turn-On Time ($V_D = \text{Rated } V_{DRM}, I_{TM} = 16 \text{ A Peak, } I_G = 30 \text{ mA}$)	t_{gt}	—	1.5	—	μs

DYNAMIC CHARACTERISTICS

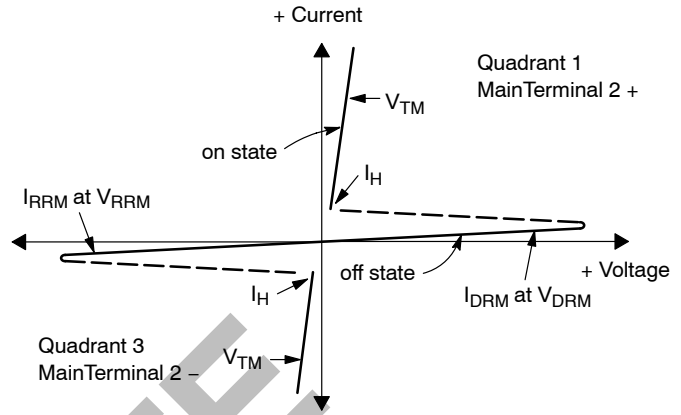
Critical Rate of Rise of Off-State Voltage ($V_D = \text{Rated } V_{DRM}, \text{ Exponential Waveform, } T_C = 110^{\circ}\text{C}$)	dv/dt	—	25	—	$\text{V}/\mu\text{s}$
Critical Rate of Rise of Commutation Voltage ($V_D = \text{Rated } V_{DRM}, I_{TM} = 11.3 \text{ A,}$ Commutating $di/dt = 4.1 \text{ A/ms, Gate Unenergized, } T_C = 80^{\circ}\text{C}$)	$dv/dt(c)$	—	5.0	—	$\text{V}/\mu\text{s}$

(1) Ratings apply for open gate conditions. Devices shall not be tested with a constant current source for blocking voltage such that the voltage applied exceeds the rated blocking voltage.

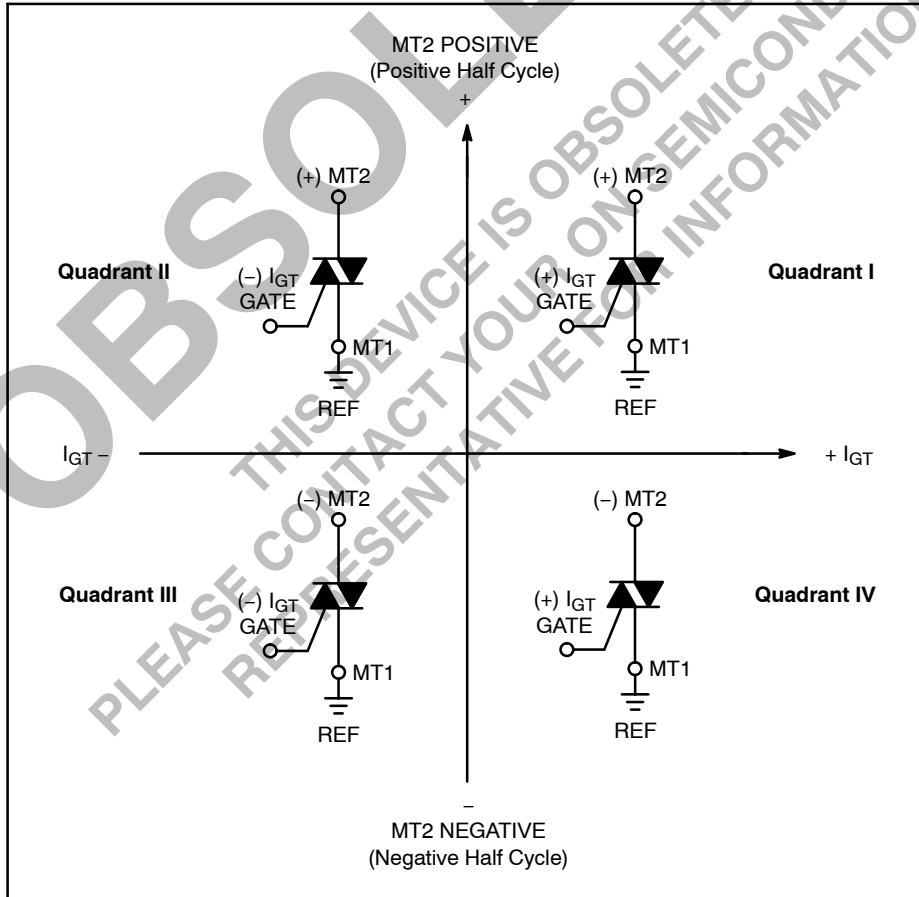
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Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I_H	Holding Current



Quadrant Definitions for a Triac



All polarities are referenced to MT1.
With in-phase signals (using standard AC lines) quadrants I and III are used.

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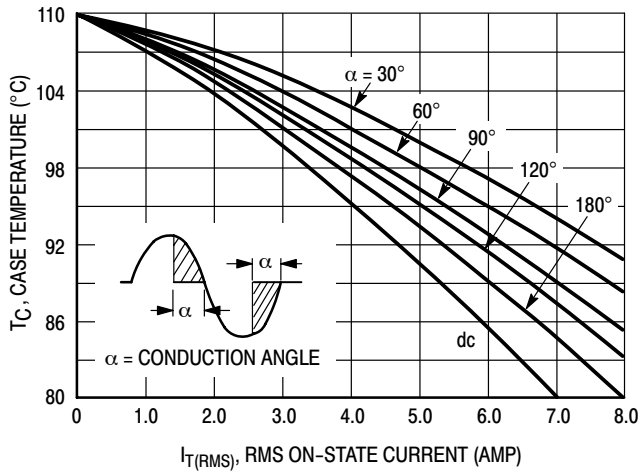


Figure 1. RMS Current Derating

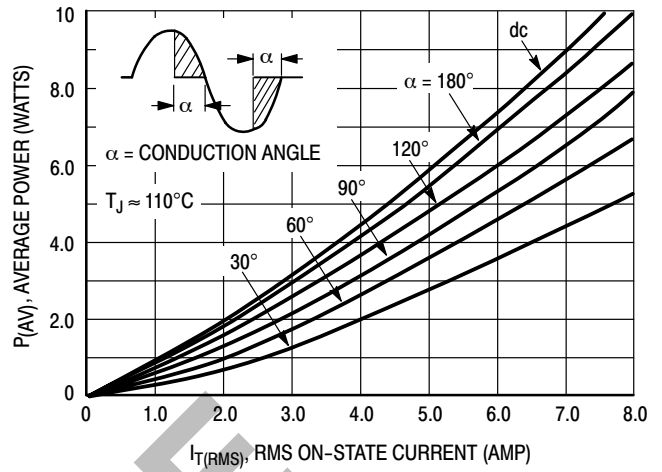


Figure 2. On-State Power Dissipation

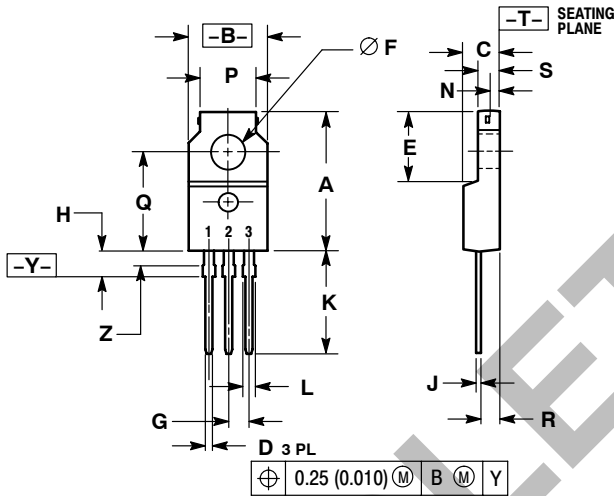
OBSOLETE

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PLEASE CONTACT YOUR ON SEMICONDUCTOR
REPRESENTATIVE FOR INFORMATION

MAC229A8FP, MAC229A10FP

PACKAGE DIMENSIONS

ISOLATED TO-220 Full Pack CASE 221C-02 ISSUE C



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. LEAD DIMENSIONS UNCONTROLLED WITHIN DIMENSION Z.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.680	0.700	17.28	17.78
B	0.388	0.408	9.86	10.36
C	0.175	0.195	4.45	4.95
D	0.025	0.040	0.64	1.01
E	0.340	0.355	8.64	9.01
F	0.140	0.150	3.56	3.81
G	0.100 BSC		2.54 BSC	
H	0.110	0.155	2.80	3.93
J	0.018	0.028	0.46	0.71
K	0.500	0.550	12.70	13.97
L	0.045	0.070	1.15	1.77
N	0.049	---	1.25	---
P	0.270	0.290	6.86	7.36
Q	0.480	0.500	12.20	12.70
R	0.090	0.120	2.29	3.04
S	0.105	0.115	2.67	2.92
Z	0.070	0.090	1.78	2.28

STYLE 3:

1. MT 1
2. MT 2
3. GATE

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